

IN THE CLAIMS:

Please cancel claims 1-37 and add new claims 38-57.

1-37. (Canceled)

38. (New) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a substrate;

forming a wiring electrically connected to the semiconductor film; and

forming a pixel electrode electrically connected to the wiring,

wherein the wiring includes a first layer comprising chromium and a second layer comprising aluminum thereon,

wherein the first layer and the second layer are continuously formed by sputtering,

wherein the first layer is in contact with the semiconductor film, and

wherein the pixel electrode is in contact with the first layer.

39. (New) A method according to claims 38, wherein the pixel electrode comprises indium tin oxide.

40. (New) A method for manufacturing a semiconductor device comprising the steps of:

forming a channel region over a substrate;

forming a source region and drain regions in contact with the channel region;

forming a wiring electrically connected to one of the source region and the drain region; and

forming a pixel electrode electrically connected to the wiring,

wherein the wiring includes a first layer comprising chromium and a second layer comprising aluminum thereon,

wherein the first layer and the second layer are continuously formed by sputtering,

wherein the first layer is in contact with one of the source region and the drain region,

and

wherein the pixel electrode is in contact with the first layer.

41. (New) A method according to claims 40, wherein the pixel electrode comprises indium tin oxide.

42. (New) A method for manufacturing a semiconductor device comprising the steps of:  
forming a semiconductor film over a substrate;  
forming a wiring electrically connected to the semiconductor film; and  
forming a pixel electrode electrically connected to the wiring,  
wherein the wiring includes a first layer comprising chromium and a second layer comprising aluminum thereon,  
wherein the first layer and the second layer are continuously formed by sputtering,  
wherein a thickness of the second layer is larger than that of the first layer,  
wherein the first layer is in contact with the semiconductor film, and  
wherein the pixel electrode is in contact with the first layer.

43. (New) A method according to claims 42, wherein the pixel electrode comprises indium tin oxide.

44. (New) A method for manufacturing a semiconductor device comprising the steps of:  
forming a semiconductor film over a substrate;  
forming a wiring electrically connected to the semiconductor film; and  
forming a pixel electrode electrically connected to the wiring,  
wherein the wiring includes a first layer comprising chromium and a second layer comprising aluminum thereon,  
wherein the first layer and the second layer are continuously formed by sputtering,  
wherein a thickness of the first layer is 20 to 200 nm and that of the second layer is 100 to 2000 nm,  
wherein the first layer is in contact with the semiconductor film, and  
wherein the pixel electrode is in contact with the first layer.

45. (New) A method according to claims 44, wherein the pixel electrode comprises indium tin oxide.

46. (New) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a substrate;

forming a leveling film over the semiconductor film;

forming a wiring over the leveling film and electrically connected to the semiconductor film through a contact hole of the leveling film; and

forming a pixel electrode over the leveling film and electrically connected to the wiring,

wherein the wiring includes a first layer comprising chromium and a second layer comprising aluminum thereon,

wherein the first layer and the second layer are continuously formed by sputtering,

wherein the first layer is in contact with the semiconductor film, and

wherein the pixel electrode is in contact with the first layer.

47. (New) A method according to claims 46, wherein the pixel electrode comprises indium tin oxide.

48. (New) A method according to claim 46, wherein the leveling film comprises an organic resin.

49. (New) A method for manufacturing a semiconductor device comprising the steps of:

forming a channel region over a substrate;

forming a source region and drain regions in contact with the channel region;

forming a leveling film over the channel region, the source region and the drain regions;

forming a wiring over the leveling film and electrically connected to one of the source region and the drain region through a contact hole of the leveling film; and

forming a pixel electrode over the leveling film and electrically connected to the wiring,

wherein the wiring includes a first layer comprising chromium and a second layer comprising aluminum thereon,

wherein the first layer and the second layer are continuously formed by sputtering,  
wherein the first layer is in contact with one of the source region and the drain region,  
and  
wherein the pixel electrode is in contact with the first layer.

50. (New) A method according to claims 49, wherein the pixel electrode comprises indium tin oxide.

51. (New) A method according to claim 49, wherein the leveling film comprises an organic resin.

52. (New) A method for manufacturing a semiconductor device comprising the steps of:  
forming a semiconductor film over a substrate;  
forming a leveling film over the semiconductor film;  
forming a wiring over the leveling film and electrically connected to the semiconductor film through a contact hole of the leveling film; and  
  
forming a pixel electrode over the leveling film and electrically connected to the wiring,  
wherein the wiring includes a first layer comprising chromium and a second layer comprising aluminum thereon,  
wherein the first layer and the second layer are continuously formed by sputtering,  
wherein a thickness of the second layer is larger than that of the first layer,  
wherein the first layer is in contact with the semiconductor film, and  
wherein the pixel electrode is in contact with the first layer.

53. (New) A method according to claims 52, wherein the pixel electrode comprises indium tin oxide.

54. (New) A method according to claim 52, wherein the leveling film comprises an organic resin.

55. (New) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a substrate;

forming a leveling film over the semiconductor film;

forming a wiring over the leveling film and electrically connected to the semiconductor film through a contact hole of the leveling film; and

forming a pixel electrode over the leveling film and electrically connected to the wiring,

wherein the wiring includes a first layer comprising chromium and a second layer comprising aluminum thereon,

wherein the first layer and the second layer are continuously formed by sputtering,

wherein a thickness of the first layer is 20 to 200 nm and that of the second layer is 100 to 2000 nm,

wherein the first layer is in contact with the semiconductor film, and

wherein the pixel electrode is in contact with the first layer.

56. (New) A method according to claims 55, wherein the pixel electrode comprises indium tin oxide.

57. (New) A method according to claim 55, wherein the leveling film comprises an organic resin.